

Wei-Chun Hung

List of Publications by Year in descending order

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Version: 2024-02-01

16
papers

62
citations

1684129

5
h-index

1720014

7
g-index

16
all docs

16
docs citations

16
times ranked

57
citing authors

#	ARTICLE	IF	CITATIONS
1	Abnormal On-Current Degradation Under Non-Conductive Stress in Contact Field Plate Lateral Double-Diffused Metal-Oxide-Semiconductor Transistor With 0.13- μ m Bipolar-CMOS-DMOS Technology. IEEE Electron Device Letters, 2022, 43, 769-772.	3.9	5
2	Abnormal trend in hot carrier degradation with fin profile in short channel FinFET devices at 14 nm node. Semiconductor Science and Technology, 2022, 37, 045010.	2.0	1
3	Suppressing Drain-Induced Barrier Lowering and Kink Effect in Low-Temperature Poly-Si TFTs Using a Partitioned Light Shield. IEEE Electron Device Letters, 2022, 43, 576-579.	3.9	0
4	Analysis of abnormal threshold voltage shift induced by surface donor state in GaN HEMT on SiC substrate. Applied Physics Letters, 2022, 120, 233505.	3.3	3
5	Analysis of Edge Effect Occurring in Non-Volatile Ferroelectric Transistors. IEEE Electron Device Letters, 2021, 42, 315-318.	3.9	7
6	Abnormal hump in low temperature in SiGe devices with silicon capping insertion layer. Journal Physics D: Applied Physics, 2021, 54, 415105.	2.8	0
7	Investigation of degradation behavior under negative bias temperature stress in Si/Si _{0.8} Ge _{0.2} metal-oxide-semiconductor capacitors. Journal Physics D: Applied Physics, 2021, 54, 475103.	2.8	1
8	Comparison of the Hot Carrier Degradation of N- and P-Type Fin Field-Effect Transistors in 14-nm Technology Nodes. IEEE Electron Device Letters, 2021, 42, 1420-1423.	3.9	6
9	Highly-Doped Region Optimization for Reduced Hot-Carrier Effects in Dual-Gate Low Temperature Polysilicon TFTs. IEEE Electron Device Letters, 2021, 42, 1794-1797.	3.9	2
10	Abnormal Increment Substrate Current After Hot Carrier Stress in n-FinFET. IEEE Electron Device Letters, 2020, 41, 15-18.	3.9	6
11	Leakage Current in Fast Recovery Diode Suppressed by Low Temperature Supercritical Fluid Treatment Process. IEEE Electron Device Letters, 2020, 41, 1540-1543.	3.9	4
12	Investigation of HCD- and NBTI-Induced Ultralow Electric Field GIDL in 14-nm Technology Node FinFETs. IEEE Transactions on Electron Devices, 2020, 67, 2697-2701.	3.0	5
13	Advanced Low-Temperature High-Pressure Hydrogen Treatment for Interface Defect Passivation in Si- and SiGe-Channel MOSCAPs. IEEE Transactions on Electron Devices, 2020, 67, 5403-5407.	3.0	12
14	A Study of Effects of Metal Gate Composition on Performance in Advanced n-MOSFETs. IEEE Transactions on Electron Devices, 2019, 66, 3286-3289.	3.0	3
15	Abnormal Positive Bias Temperature Instability Induced by Dipole Doped N-Type MOSCAP. IEEE Journal of the Electron Devices Society, 2019, 7, 897-901.	2.1	3
16	Abnormal Relationship Between Hot Carrier Stress Degradation and Body Current in High-k Metal Gate in the 14-nm Node. IEEE Electron Device Letters, 2019, 40, 498-501.	3.9	4